



DMTH6005LPSQ

60V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D T _C = +25°C (Note 10)
60V	$5.5m\Omega @ V_{GS} = 10V$	100A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- **High Frequency Switching**
- Sync. Rectification
- **DCDC** Converters

Features

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching ensures more reliable and robust end application
- Low $R_{DS(ON)}$ minimizes power losses
- Low Q_g minimizes switching losses Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

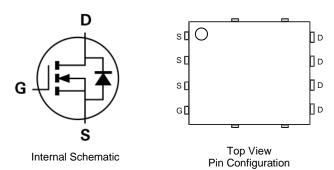
Mechanical Data

- Case: PowerDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)



Top View

Bottom View



Ordering Information (Note 5)

Part Number	Case	Packaging
DMTH6005LPSQ-13	PowerDI5060-8	2,500 / Tape & Reel

1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied. Notes: 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

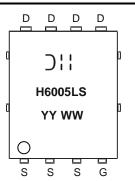
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Please refer to https://www.diodes.com/quality/.

Pin1

5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



) | | = Manufacturer's Marking H6005LS = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 18 = 2018) WW = Week (01 to 53)

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	60	V	
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Drain Current (Note 6)	T _A = +25°C T _A = +70°C	ID	20.6 17.2	A
Continuous Drain Current (Note 7)	T _C = +25°C (Note 10)	ID	100	А
	$T_{C} = +100^{\circ}C$		90	
Maximum Continuous Body Diode Forward Current (Note 7)		Is	100	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	160	A
Avalanche Current, L = 1mH		I _{AS}	14.8	A
Avalanche Energy, L = 1mH		E _{AS}	98	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	T _A = +25°C	PD	3.2	W
Thermal Resistance, Junction to Ambient (Note 6)		R _{0JA}	47	°C/W
Total Power Dissipation (Note 7)	T _C = +25°C	PD	150	W
Thermal Resistance, Junction to Case (Note 7)		R _{0JC}	1	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +175	°C

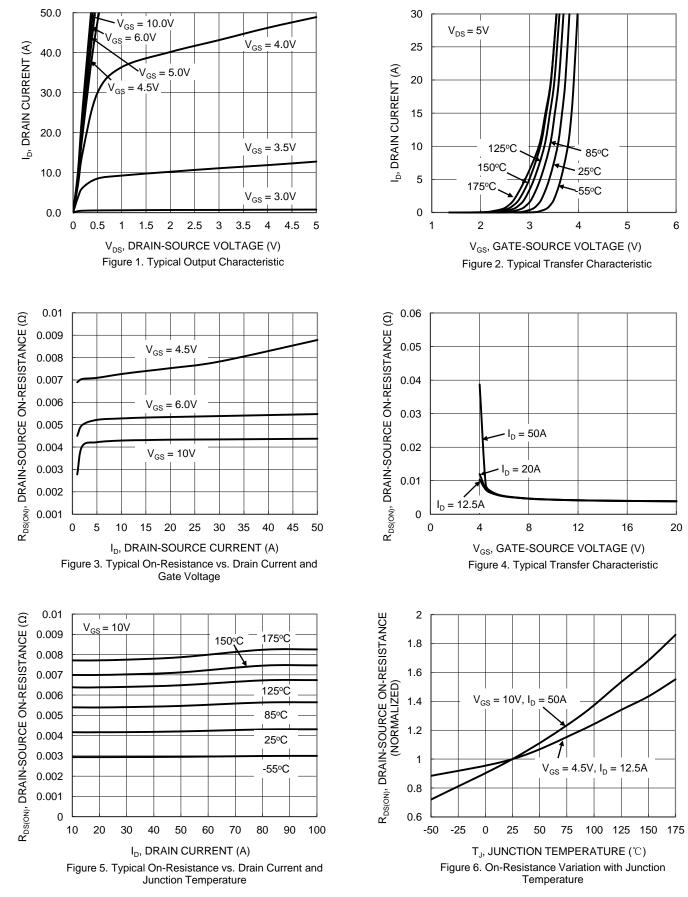
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	—	V	$V_{GS} = 0V, I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	-	—	1	μA	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)	·						
Gate Threshold Voltage	V _{GS(TH)}	1	—	3	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
			4.4	5.5	mΩ	$V_{GS} = 10V, I_D = 50A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	5.7	7.2		$V_{GS} = 6V, I_D = 20A$	
		_	7.7	10		V _{GS} = 4.5V, I _D = 12.5A	
Diode Forward Voltage	V _{SD}	_	0.9	_	V	$V_{GS} = 0V, I_{S} = 50A$	
DYNAMIC CHARACTERISTICS (Note 9)	·					-	
Input Capacitance	C _{iss}		2962	_		$V_{DS} = 30V, V_{GS} = 0V,$ f = 1MHz	
Output Capacitance	Coss	—	965.2	—	pF		
Reverse Transfer Capacitance	Crss	_	59.8	—			
Gate Resistance	Rg	_	0.66	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V _{GS} = 10V)	Qg	_	47.1	_		V _{DD} = 30V, I _D = 50A	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	23.1	—	nC		
Gate-Source Charge	Q _{gs}	_	10.2	_	nc		
Gate-Drain Charge	Q _{gd}	_	12.5	_			
Turn-On Delay Time	t _{D(ON)}		8.3	_		$V_{DD} = 30V, V_{GS} = 10V,$ $I_D = 30A, R_G = 3.3\Omega$	
Turn-On Rise Time	t _R		9.4	_			
Turn-Off Delay Time	t _{D(OFF)}		22	_	ns		
Turn-Off Fall Time	t _F	_	8.9	—			
Body Diode Reverse Recovery Time	t _{RR}	_	40.4	—	ns		
Body Diode Reverse Recovery Charge	Q _{RR}	_	49.7	_	nC	I _F = 30A, di/dt = 100A/μs	

 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
7. Thermal resistance from junction to soldering point (on the exposed drain pad).
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.
10. Package limited. Notes:

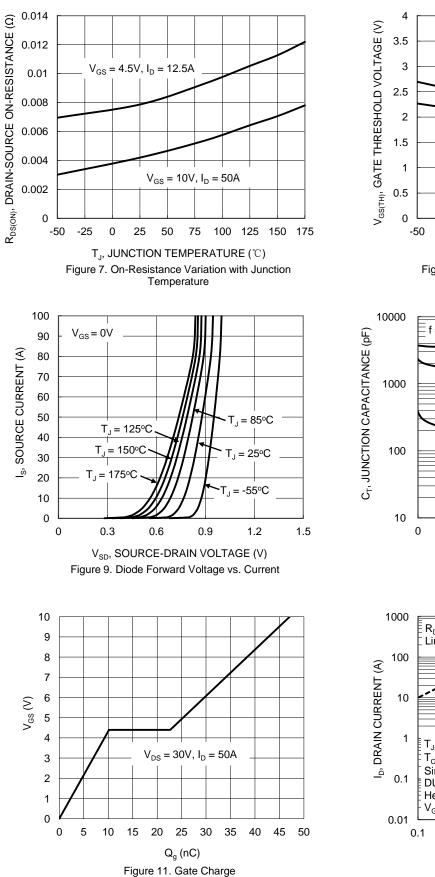


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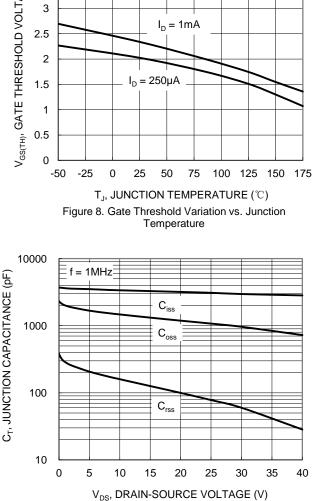
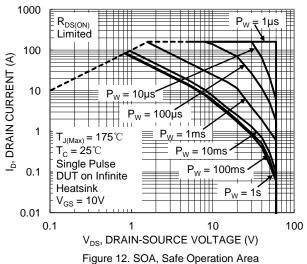
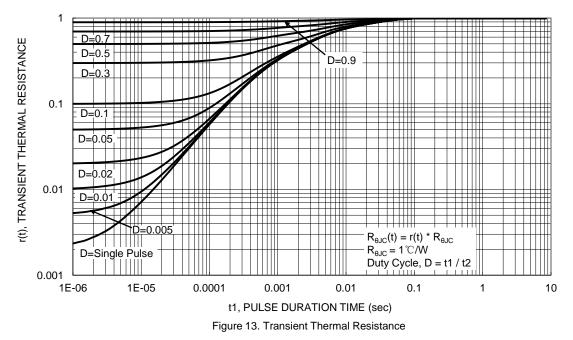


Figure 10. Typical Junction Capacitance





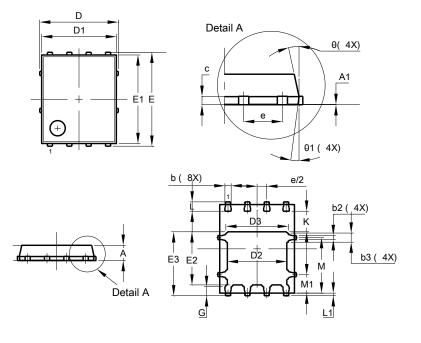




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8

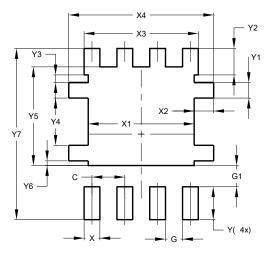


	PowerDI5060-8					
Dim	Min	Max	Тур			
Α	0.90	1.10	1.00			
A1	0.00	0.05	-			
b	0.33	0.51	0.41			
b2	0.200	0.350	0.273			
b3	0.40	0.80	0.60			
С	0.230	0.330	0.277			
D		5.15 BSC				
D1	4.70	5.10	4.90			
D2	3.70	4.10	3.90			
D3	3.90	4.30	4.10			
E	(6.15 BSC	;			
E1	5.60	6.00	5.80			
E2	3.28	3.68	3.48			
E3	3.99	4.39	4.19			
е	1.27 BSC					
G	0.51	0.71	0.61			
К	0.51	-	-			
L	0.51	0.71	0.61			
L1	0.100	0.200	0.175			
М	3.235	4.035	3.635			
M1	1.00	1.40	1.21			
Θ	10°	12°	11°			
Θ1	6°	8°	7°			
AI	All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8



Dimensions	Value (in mm)			
С	1.270			
G	0.660			
G1	0.820			
Х	0.610			
X1	4.100			
X2	0.755			
X3	4.420			
X4	5.610			
Y	1.270			
Y1	0.600			
Y2	1.020			
Y3	0.295			
Y4	1.825			
Y5	3.810			
Y6	0.180			
Y7	6.610			



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